

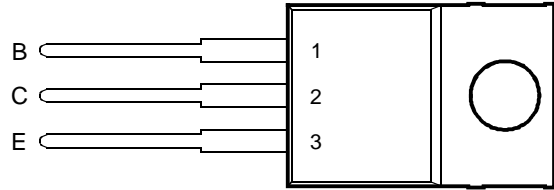
TIP110, TIP111, TIP112 NPN SILICON POWER DARLINGTONS

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DECEMBER 1971 - REVISED MARCH 1997

- Designed for Complementary Use with TIP115, TIP116 and TIP117
- 50 W at 25°C Case Temperature
- 4 A Continuous Collector Current
- Minimum h_{FE} of 500 at 4 V, 2 A

TO-220 PACKAGE
(TOP VIEW)



Pin 2 is in electrical contact with the mounting base.

MDTRACA

absolute maximum ratings at 25°C case temperature (unless otherwise noted)

| RATING | | SYMBOL | VALUE | UNIT |
|--|--------|---------------------|-------------|------|
| Collector-base voltage ($I_E = 0$) | TIP110 | V_{CBO} | 60 | V |
| | TIP111 | | 80 | |
| | TIP112 | | 100 | |
| Collector-emitter voltage ($I_B = 0$) | TIP110 | V_{CEO} | 60 | V |
| | TIP111 | | 80 | |
| | TIP112 | | 100 | |
| Emitter-base voltage | | V_{EBO} | 5 | V |
| Continuous collector current | | I_C | 4 | A |
| Peak collector current (see Note 1) | | I_{CM} | 6 | A |
| Continuous base current | | I_B | 50 | mA |
| Continuous device dissipation at (or below) 25°C case temperature (see Note 2) | | P_{tot} | 50 | W |
| Continuous device dissipation at (or below) 25°C free air temperature (see Note 3) | | P_{tot} | 2 | W |
| Unclamped inductive load energy (see Note 4) | | $\frac{1}{2}LI_C^2$ | 25 | mJ |
| Operating junction temperature range | | T_j | -65 to +150 | °C |
| Storage temperature range | | T_{stg} | -65 to +150 | °C |
| Lead temperature 3.2 mm from case for 10 seconds | | T_L | 260 | °C |

- NOTES: 1. This value applies for $t_p \leq 0.3$ ms, duty cycle $\leq 10\%$.
2. Derate linearly to 150°C case temperature at the rate of 0.4 W/°C.
3. Derate linearly to 150°C free air temperature at the rate of 16 mW/°C.
4. This rating is based on the capability of the transistor to operate safely in a circuit of: $L = 20$ mH, $I_{B(on)} = 5$ mA, $R_{BE} = 100 \Omega$, $V_{BE(off)} = 0$, $R_S = 0.1 \Omega$, $V_{CC} = 20$ V.

PRODUCT INFORMATION

Information is current as of publication date. Products conform to specifications in accordance with the terms of Power Innovations standard warranty. Production processing does not necessarily include testing of all parameters.



TIP110, TIP111, TIP112

NPN SILICON POWER DARLINGTONS

DECEMBER 1971 - REVISED MARCH 1997

electrical characteristics at 25°C case temperature

| PARAMETER | TEST CONDITIONS | MIN | TYP | MAX | UNIT |
|--|---|---|-----|-------------|------|
| $V_{(BR)CEO}$ Collector-emitter breakdown voltage | $I_C = 30 \text{ mA}$ $I_B = 0$ (see Note 5) | TIP110 60 TIP111 80 TIP112 100 | | | V |
| I_{CEO} Collector-emitter cut-off current | $V_{CE} = 30 \text{ V}$ $V_{CE} = 40 \text{ V}$ $V_{CE} = 50 \text{ V}$ $I_B = 0$ | TIP110 TIP111 TIP112 | | 2 2 2 | mA |
| I_{CBO} Collector cut-off current | $V_{CB} = 60 \text{ V}$ $V_{CB} = 80 \text{ V}$ $V_{CB} = 100 \text{ V}$ $I_E = 0$ | TIP110 TIP111 TIP112 | | 1 1 1 | mA |
| I_{EBO} Emitter cut-off current | $V_{EB} = 5 \text{ V}$ $I_C = 0$ | | | 2 | mA |
| h_{FE} Forward current transfer ratio | $V_{CE} = 4 \text{ V}$ $V_{CE} = 4 \text{ V}$ $I_C = 1 \text{ A}$ $I_C = 2 \text{ A}$ (see Notes 5 and 6) | 1000 500 | | | |
| $V_{CE(sat)}$ Collector-emitter saturation voltage | $I_B = 8 \text{ mA}$ $I_C = 2 \text{ A}$ (see Notes 5 and 6) | | | 2.5 | V |
| V_{BE} Base-emitter voltage | $V_{CE} = 4 \text{ V}$ $I_C = 2 \text{ A}$ (see Notes 5 and 6) | | | 2.8 | V |
| V_{EC} Parallel diode forward voltage | $I_E = 4 \text{ A}$ $I_B = 0$ (see Notes 5 and 6) | | | 3.5 | V |

NOTES: 5. These parameters must be measured using pulse techniques, $t_p = 300 \mu\text{s}$, duty cycle $\leq 2\%$.

6. These parameters must be measured using voltage-sensing contacts, separate from the current carrying contacts.

resistive-load-switching characteristics at 25°C case temperature

| PARAMETER | TEST CONDITIONS [†] | MIN | TYP | MAX | UNIT |
|-------------------------|---|-----|-----|-----|---------------|
| t_{on} Turn-on time | $I_C = 2 \text{ A}$ $I_{B(on)} = 8 \text{ mA}$ $I_{B(off)} = -8 \text{ mA}$ | | 2.6 | | μs |
| t_{off} Turn-off time | $V_{BE(off)} = -5 \text{ V}$ $R_L = 15 \Omega$ $t_p = 20 \mu\text{s}$, dc $\leq 2\%$ | | 4.5 | | μs |

[†] Voltage and current values shown are nominal; exact values vary slightly with transistor parameters.

PRODUCT INFORMATION

TYPICAL CHARACTERISTICS

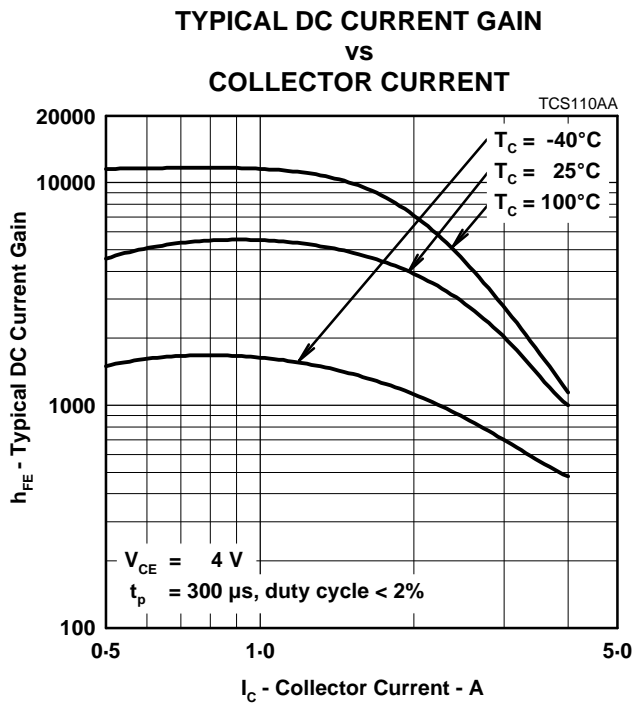


Figure 1.

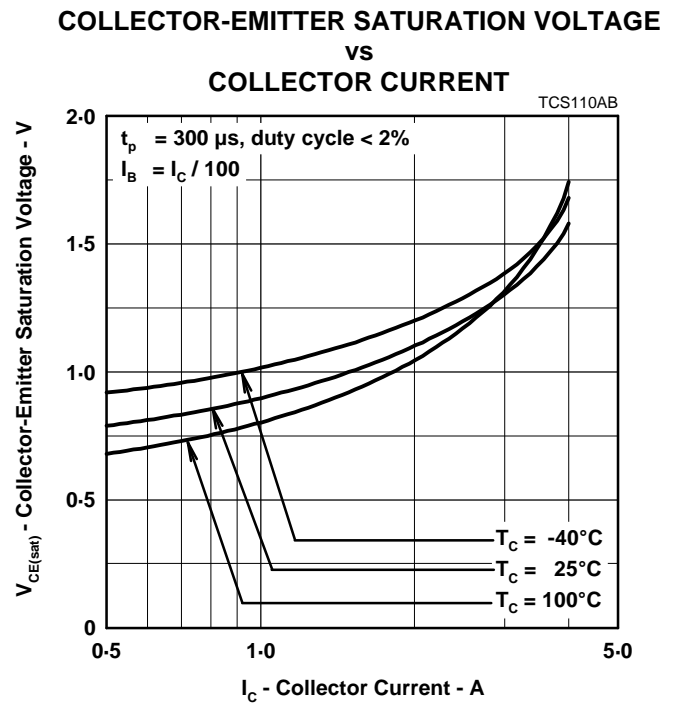


Figure 2.

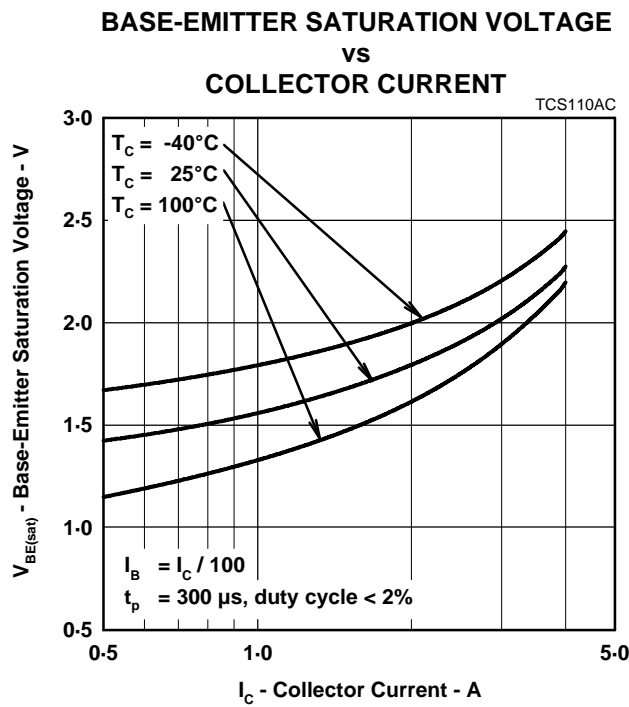


Figure 3.

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DECEMBER 1971 - REVISED MARCH 1997

MAXIMUM SAFE OPERATING REGIONS

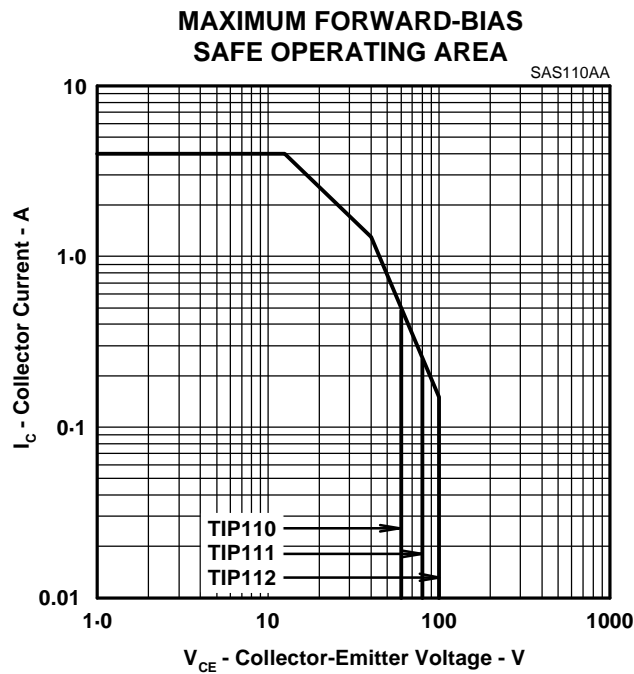


Figure 4.

THERMAL INFORMATION

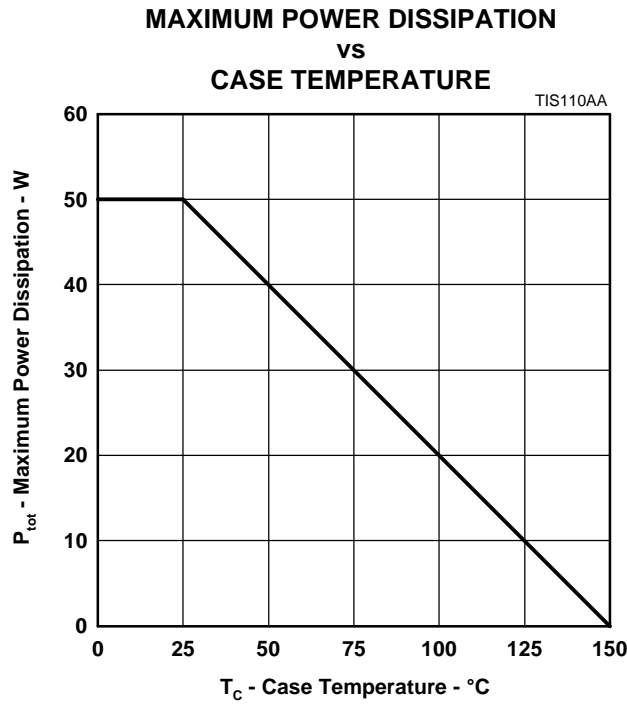


Figure 5.

PRODUCT INFORMATION

TIP110, TIP111, TIP112 NPN SILICON POWER DARLINGTONS

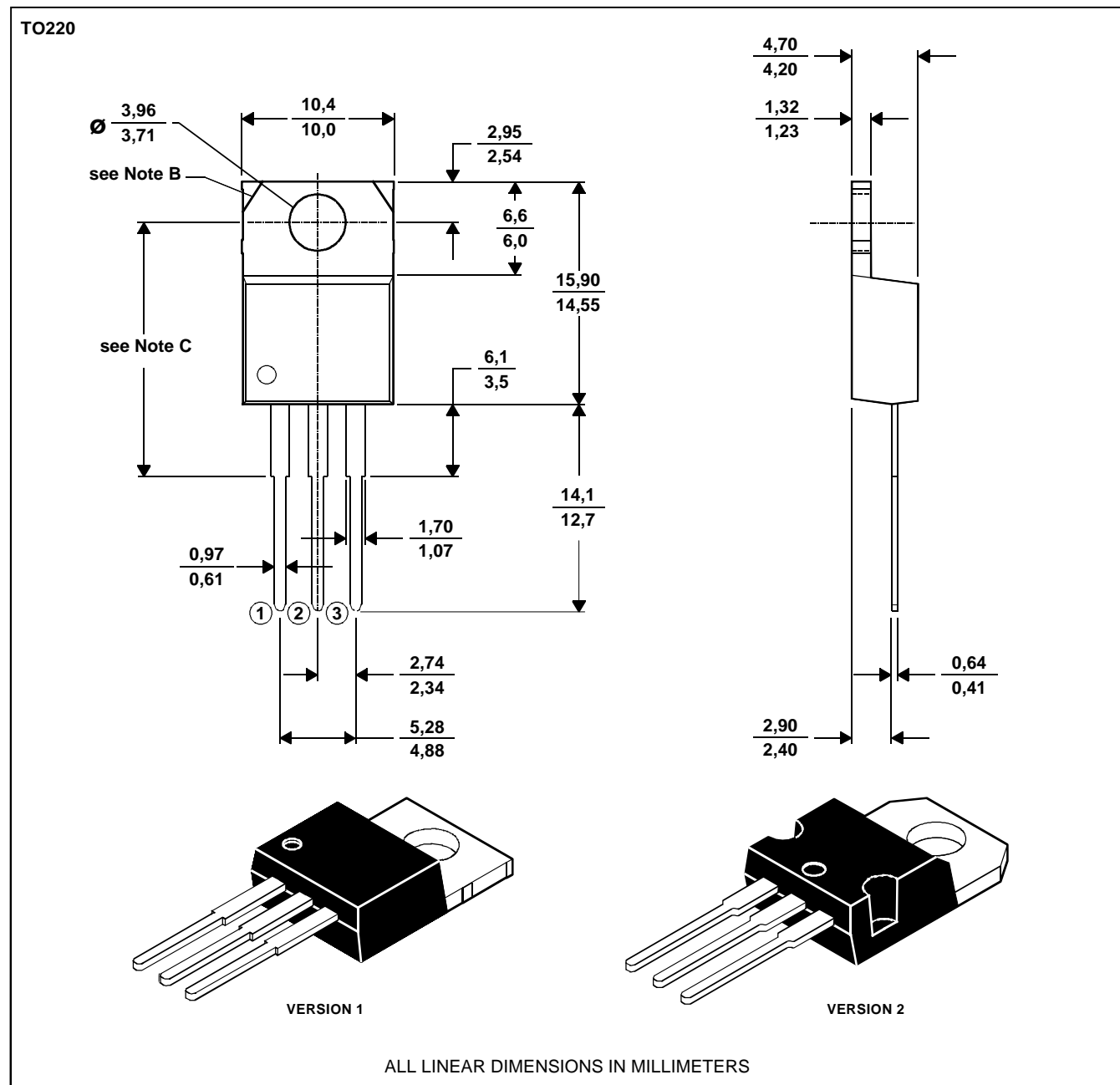
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MECHANICAL DATA

TO-220

3-pin plastic flange-mount package

This single-in-line package consists of a circuit mounted on a lead frame and encapsulated within a plastic compound. The compound will withstand soldering temperature with no deformation, and circuit performance characteristics will remain stable when operated in high humidity conditions. Leads require no additional cleaning or processing when used in soldered assembly.



NOTES: A. The centre pin is in electrical contact with the mounting tab.
B. Mounting tab corner profile according to package version.
C. Typical fixing hole centre stand off height according to package version.
Version 1, 18.0 mm. Version 2, 17.6 mm.

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